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Kind regards,

Team Nexperia



# **PBHV9115X**150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistorRev. 01 - 10 March 2010Product data sheet

### 1. Product profile

### 1.1 General description

PNP high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat Surface-Mounted Device (SMD) plastic package.

### 1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>

### **1.3 Applications**

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-150	V
I <sub>C</sub>	collector current		-	-	-1	А
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA	100	220	-	

### 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	collector		2 J
3	base		3



150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBHV9115X	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89			

### 4. Marking

#### Table 4.Marking codes

Marking code <sup>[1]</sup>	
*4G	

[1] \* = -: made in Hong Kong\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

### 5. Limiting values

#### Table 5. Limiting values

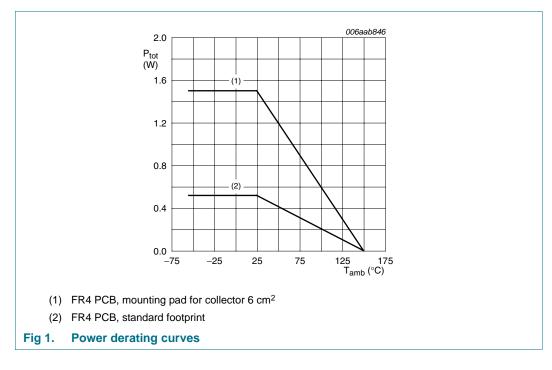
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-150	V
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-200	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-2	A
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-400	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	520	mW
			[2]	1.5	W
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



### 6. Thermal characteristics

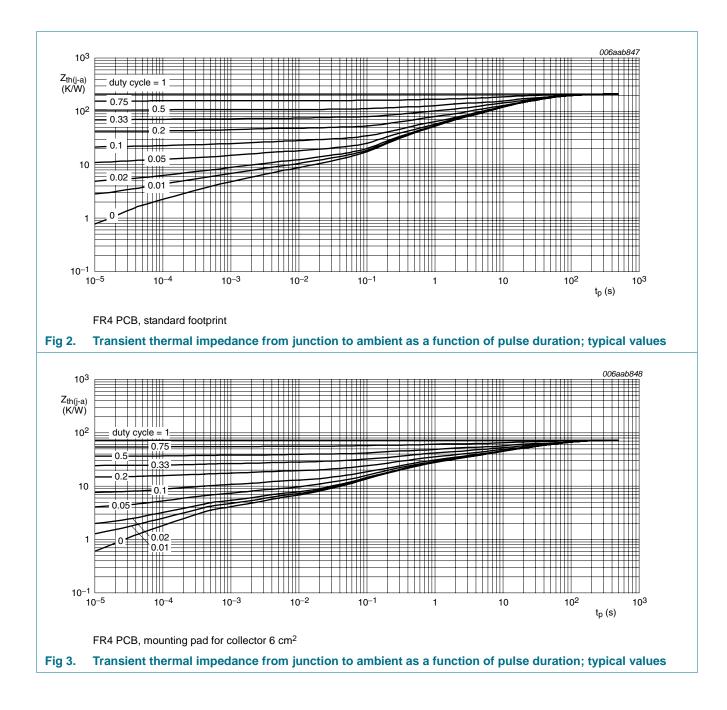
Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1]</u> -	-	240	K/W
	junction to ambient		[2] _	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

### **PBHV9115X**

150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



### 150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

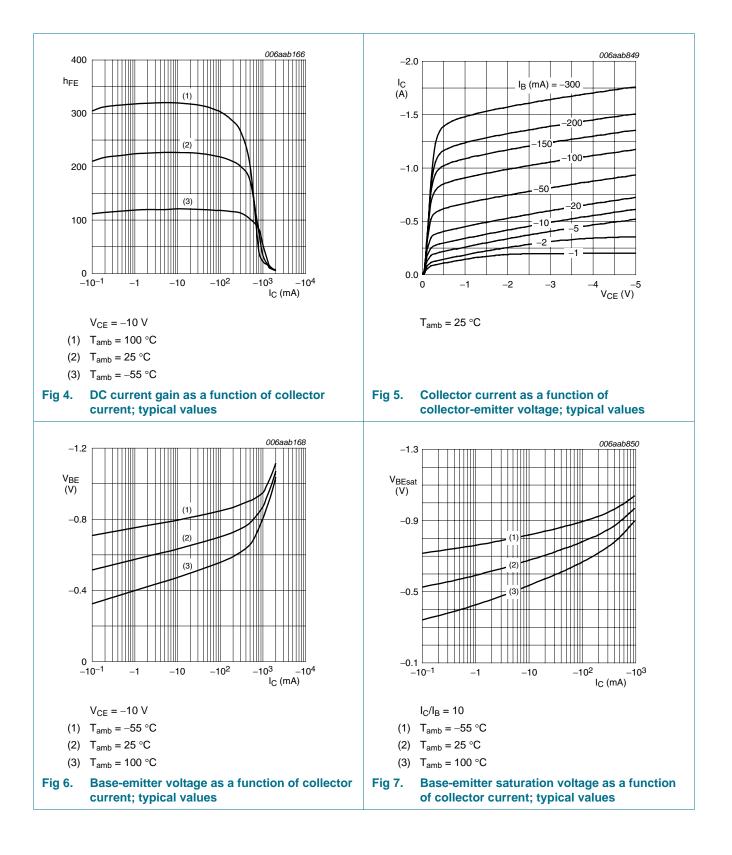
### 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -120 V;$ $I_E = 0 A$		•	-	-100	nA
		V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 V$					
		I <sub>C</sub> = -50 mA		100	220	-	
		$I_{\rm C} = -100  {\rm mA}$	[1]	100	220	-	
		$I_{\rm C} = -1$ A	[1]	10	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -100 mA; I <sub>B</sub> = -10 mA	[1]	-	-60	-120	mV
		$I_{C} = -100 \text{ mA};$ $I_{B} = -20 \text{ mA}$	<u>[1]</u>	-	-50	-100	mV
	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA	<u>[1]</u>	-	-200	-300	mV	
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -100 mA	<u>[1]</u>	-	-1	-1.2	V
t <sub>d</sub>	delay time	$V_{CC} = -6 V;$		-	8	-	ns
t <sub>r</sub>	rise time	I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -0.1 A;		-	282	-	ns
t <sub>on</sub>	turn-on time	$I_{Boff} = 0.1 \text{ A}$		-	290	-	ns
t <sub>s</sub>	storage time			-	430	-	ns
t <sub>f</sub>	fall time			-	300	-	ns
t <sub>off</sub>	turn-off time			-	730	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -10 \text{ mA};$ f = 100 MHz		-	115	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -20 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 1  MHz		-	10	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 V;$ $I_{C} = i_{c} = 0 A;$ f = 1 MHz		-	150	-	pF

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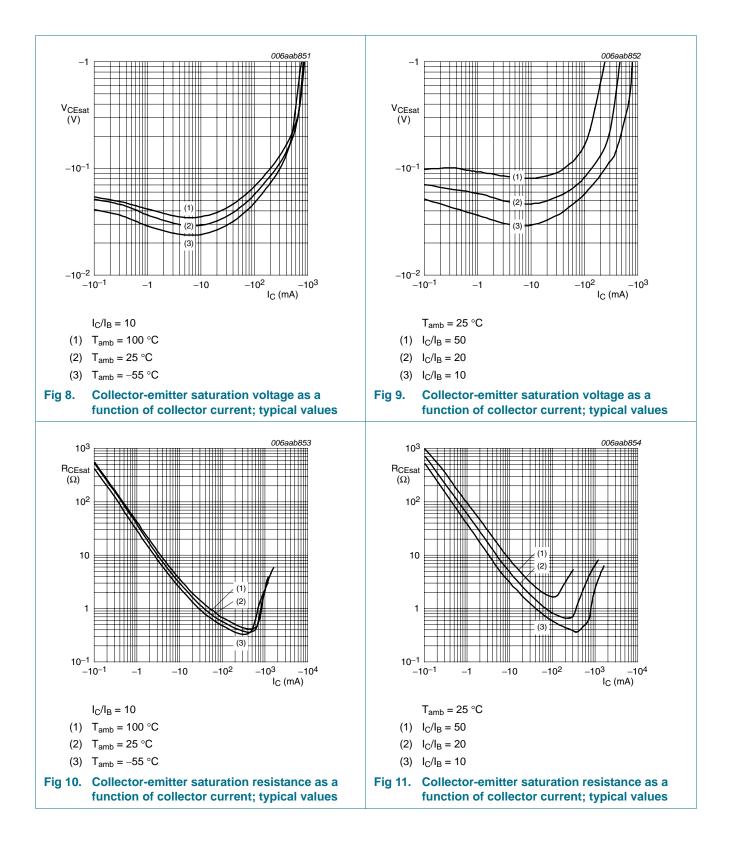
#### 150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



PBHV9115X\_1 Product data sheet

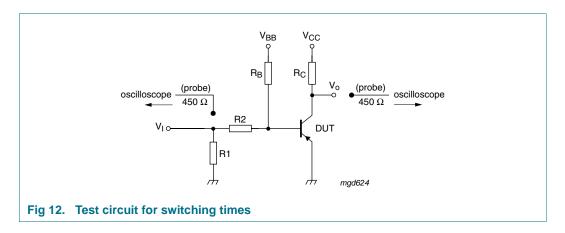
### **PBHV9115X**

#### 150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

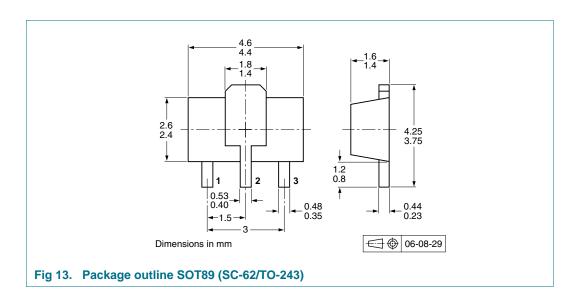


150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 8. Test information



### 9. Package outline



### **10. Packing information**

#### Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

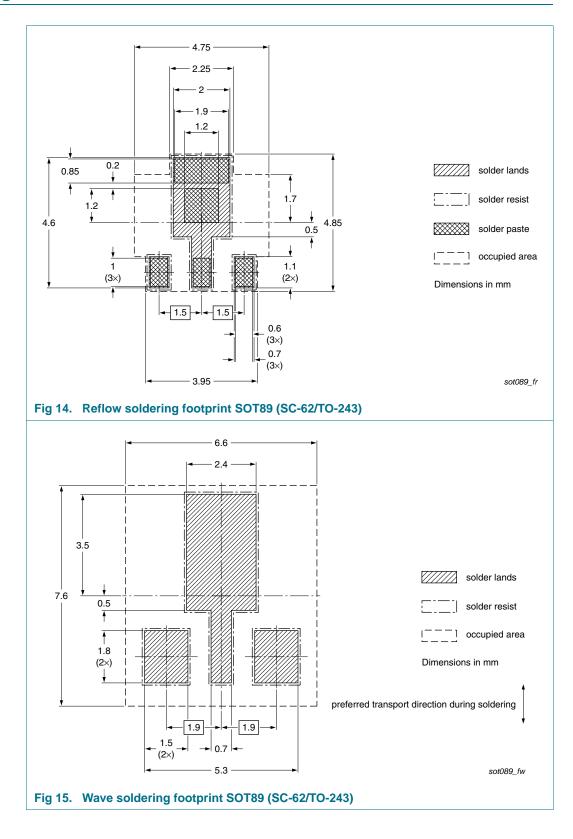
Type number	Package	Description	Packing	g quantity	
			1000	4000	
PBHV9115X	SOT89	8 mm pitch, 12 mm tape and reel; T1	l -115	-135	
		8 mm pitch, 12 mm tape and reel; T3	-120	-	

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

- [2] T1: normal taping
- [3] T3: 90° taping

150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### **11. Soldering**



PBHV9115X\_1 Product data sheet

150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### **12. Revision history**

Table 9. Revision hist	Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PBHV9115X_1	20100310	Product data sheet	-	-		

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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PBHV9115X\_1

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150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### **15. Contents**

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 1
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 3
7	Characteristics 5
8	Test information 8
9	Package outline 8
10	Packing information8
11	Soldering 9
12	Revision history 10
13	Legal information
13.1	Data sheet status 11
13.2	Definitions 11
13.3	Disclaimers
13.4	Trademarks 12
14	Contact information 12
15	Contents 13

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